WHAT IS CLAIMED IS:

1. A method of forming a semiconductor structure comprising a low-K dielectric material on a substrate comprising the steps of:

providing an environment having a regulated temperature;

placing a substrate having a top surface in said environment;

regulating said temperature of said environment to between about 0° C and 250° C;

depositing a layer of material on said top surface of said substrate wherein said layer has a dielectric constant of no more than 2.5;

regulating the temperature of said environment between 0° C and 400° C; and

curing said deposited layer of material.

2. The method of claim 1 wherein said step of depositing is a process selected from the group consisting of a CVD process and a spin-on process.

3. The method of claim 2 wherein said step of depositing is a CVD process.

4. The method of claim 2 wherein said step of depositing is a spin-on process.

5. The method of claim 1 wherein said deposited layer has a dielectric constant of between about 1.9 and 2.5.

6. The method of claim 1 wherein said step of curing is a process selected from the group consisting of a plasma treatment, an E-beam treatment and a UV treatment.

7. The method of claim 6 wherein said step of curing is a plasma treatment.

8. The method of claim 6 wherein said step of curing is a E-beam treatment.

9. The method of claim 6 wherein said step of curing is a UV treatment.

10. The method of claim 2 wherein said step of curing is a process selected from the group consisting of a plasma treatment, an E-beam treatment and a UV treatment.

11. The method of claim 9 wherein said step of curing is a plasma treatment.

12. The method of claim 9 wherein said step of curing is a E-beam treatment.

13. The method of claim 9 wherein said step of curing is a UV treatment.

14. The method of claim 9 wherein said deposited layer has a dielectric constant of between about 1.9 and 2.5.

15. The method of claim 1 wherein said environment of said curing step further includes a gas selected from the group consisting of $H_2$, $N_2$, $NH_3$, $CO_2$, all hydride gases and a mixture of said gases.

16. The method of claim 2 wherein said environment of said curing step further includes a gas selected from the group consisting of $H_2$, $N_2$, $NH_3$, $CO_2$, all hydride gases and a mixture of said gases.

17. The method of claim 6 wherein said environment of said curing step further includes a gas selected from the group consisting of $H_2$, $N_2$, $NH_3$, $CO_2$, all hydride gases and a mixture of said gases.

18. The method of claim 9 wherein said environment of said curing step further includes a gas selected from the group consisting of $H_2$, $N_2$, $NH_3$, $CO_2$, all hydride gases and a mixture of said gases.

19. The method of claim 16 wherein said deposited layer has a dielectric constant of between bout 1.9 and 2.5.